



PE8208C N-Channel Enhancement Mode Power MOSFET

PE8208C Description

The PE8208C uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. It can be used in a wide variety of applications.

PE8208C General Features

- $V_{DS} = 20V$, $I_D = 8A$

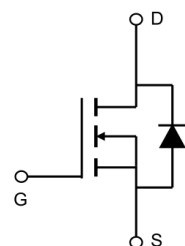
$$R_{DS(ON)} < 13m\Omega @ V_{GS}=4.5V$$

$$R_{DS(ON)} < 18m\Omega @ V_{GS}=2.5V$$

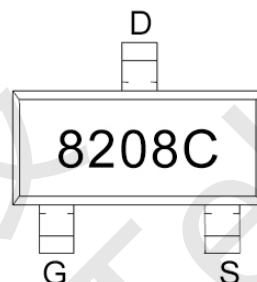
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

PE8208C Application

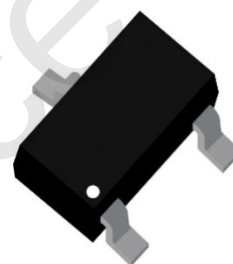
- PWM applications
- Load switch



Schematic diagram



Marking and pin assignment



SOT-23-3L

PE8208C Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	8	A
Drain Current-Continuous (TA=70°C)	I_D	5.6	A
Pulsed Drain Current (Note 1)	I_{DM}	32	A
Maximum Power Dissipation	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

PE8208C Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	°C/W
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PE8208C Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=18V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.7	1.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=6A$	-	10.5	13	m Ω
		$V_{GS}=2.5V, I_D=5A$	-	13	18	m Ω
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V,$ $F=1MHz$	-	830	-	pF
Output Capacitance	C_{oss}		-	130	-	pF
Reverse Transfer Capacitance (Note 4)	C_{rss}		-	120	-	pF
Gate Resistance	R_g	$V_{DS}=0V, V_{GS}=0V, F=1MHz$	-	1.2	-	Ω
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, R_L=1\Omega,$ $V_{GS}=4.5V, R_G=3\Omega$	-	13	-	nS
Turn-on Rise Time	t_r		-	63.8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	38	-	nS
Turn-Off Fall Time	t_f		-	8.2	-	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=6A,$ $V_{GS}=4.5V$	-	20	-	nC
Gate-Source Charge	Q_{gs}		-	1.7	-	nC
Gate-Drain Charge	Q_{gd}		-	2.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=1A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	8	A
Reverse Recovery Time	t_{rr}	$I_F=6A, di/dt=60A/\mu s$	-	29.4	-	nS
Reverse Recovery Charge	Q_{rr}		-	6.8	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to product.



PE8208C Typical Electrical and Thermal Characteristics

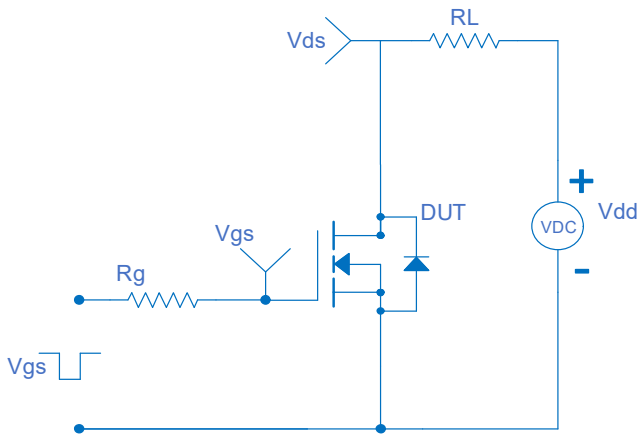


Figure 1 Switching Test Circuit

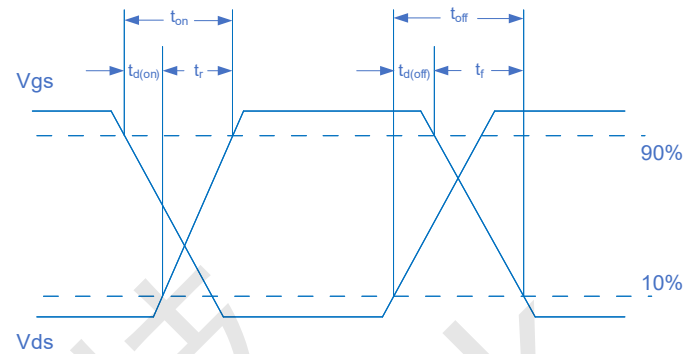


Figure 2 Switching Waveform

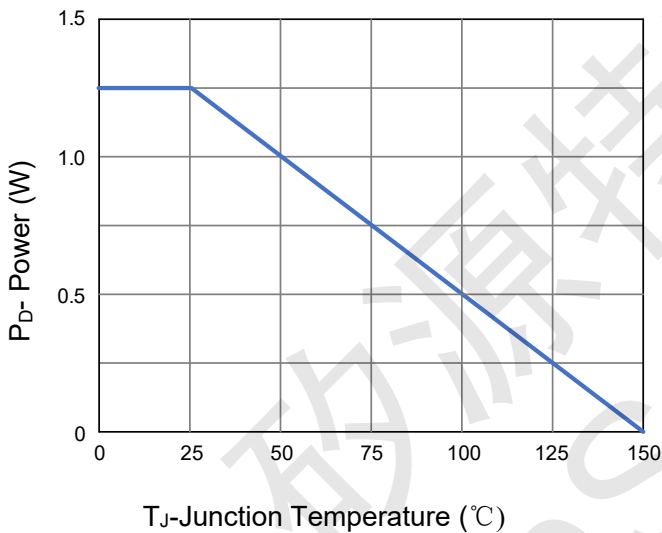


Figure 3 Power Dissipation

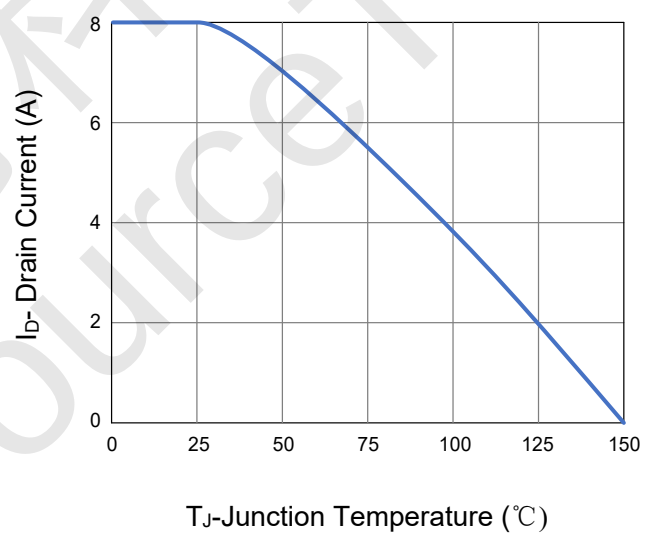


Figure 4 Drain Current

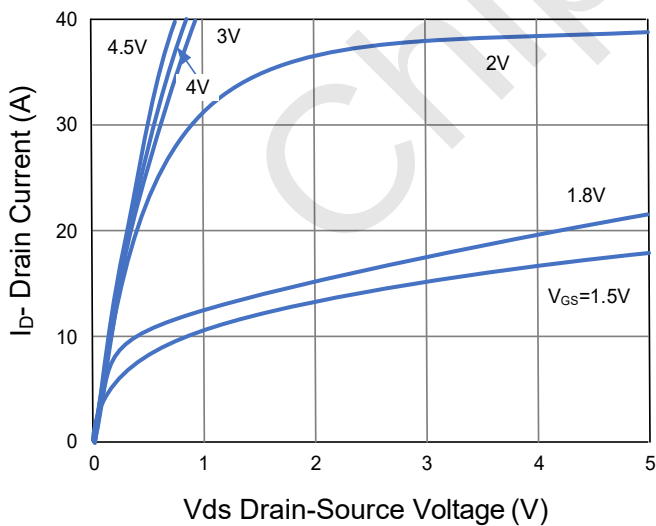


Figure 5 Output Characteristics

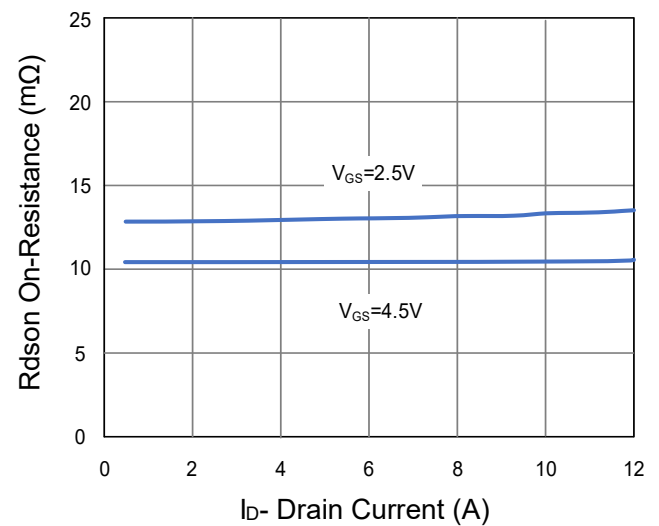
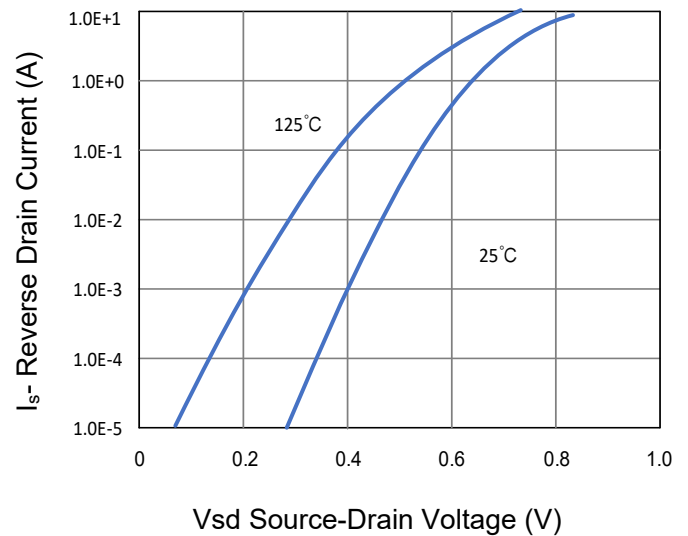
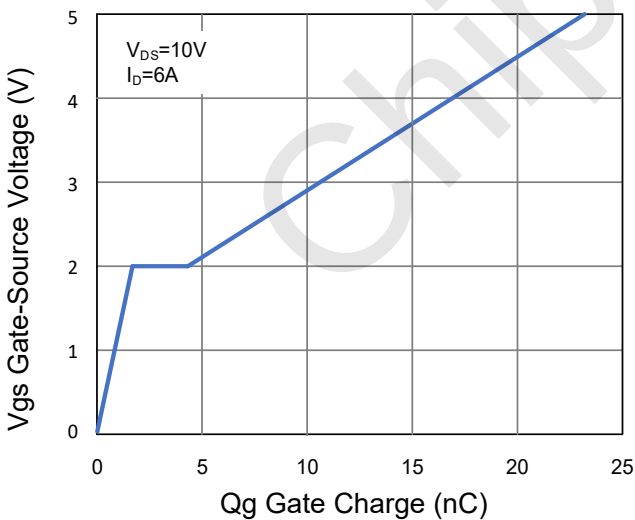
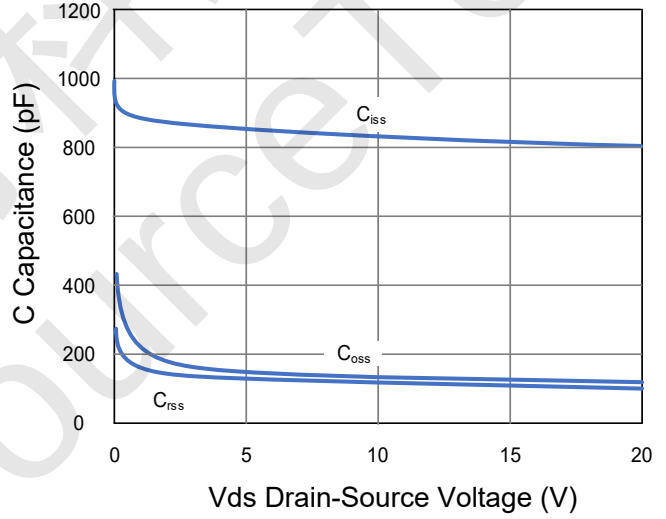
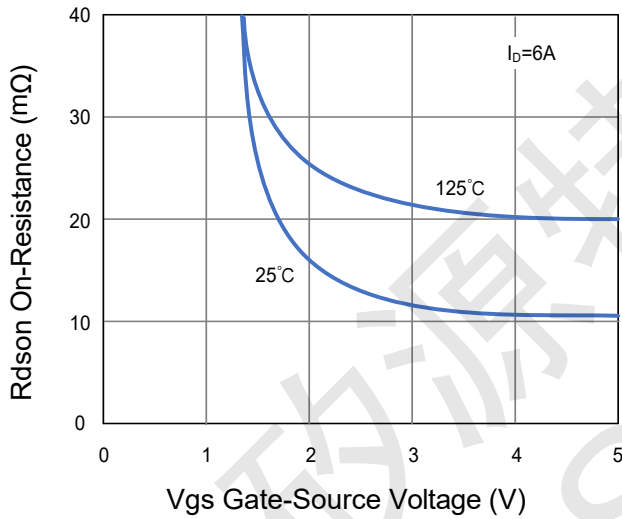
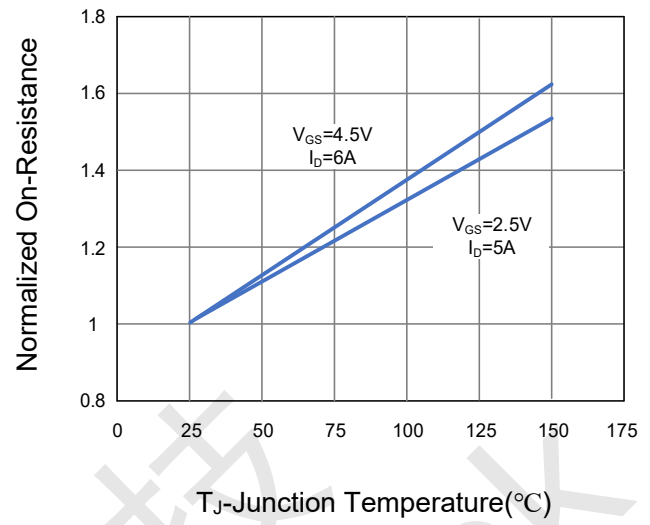
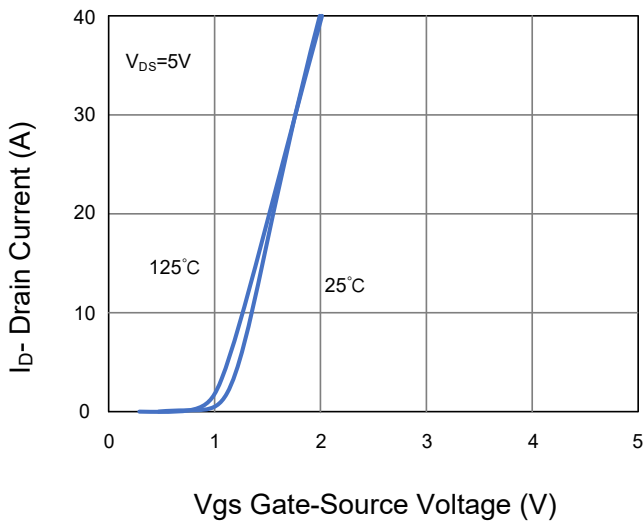


Figure 6 Rdson vs Drain Current



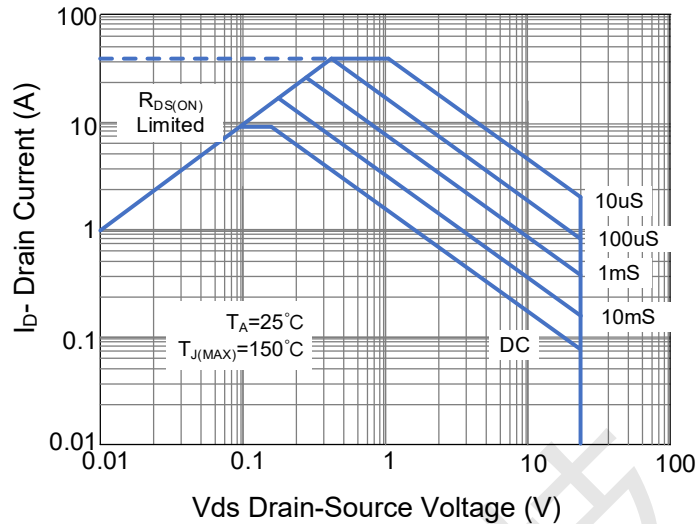


Figure 13 Safe Operation Area

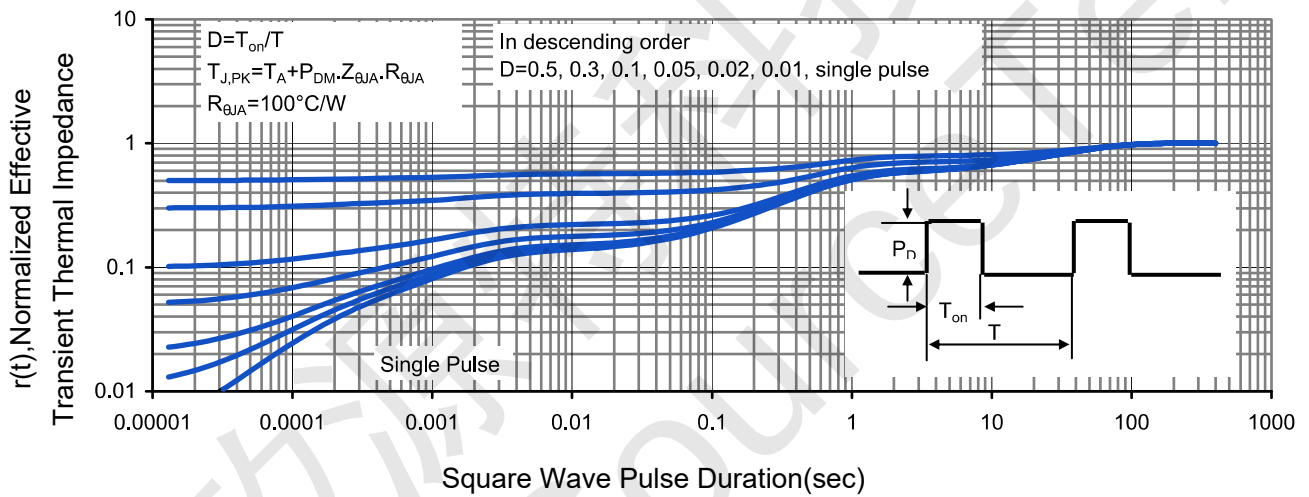
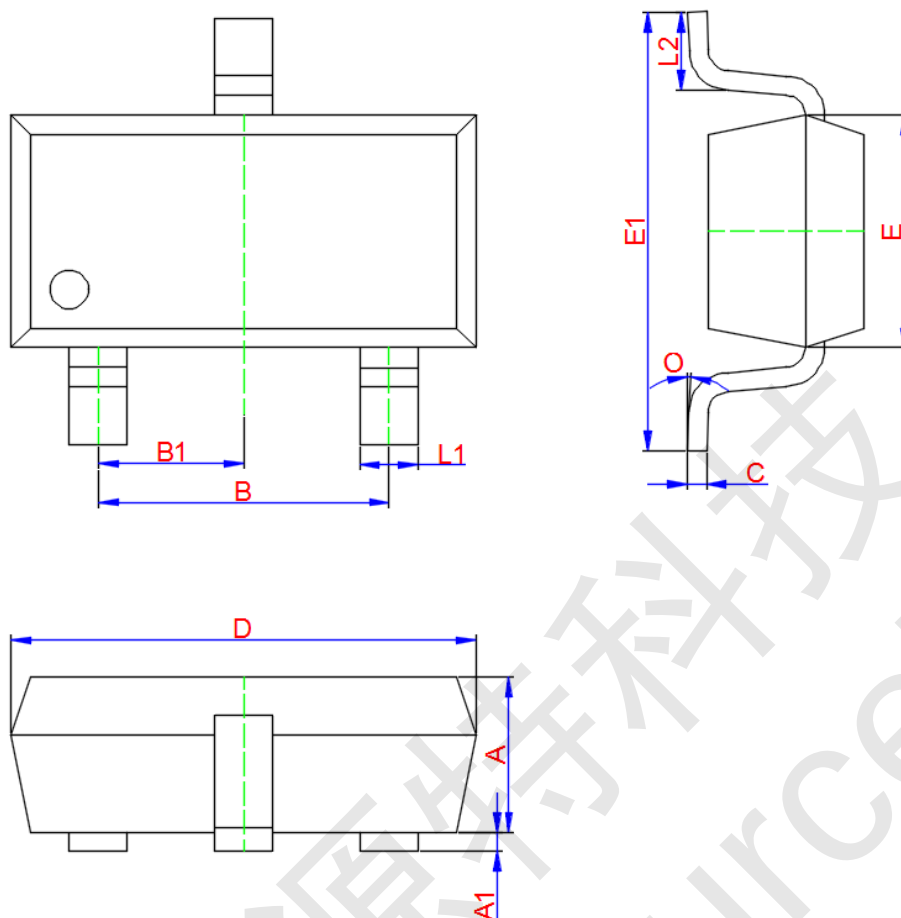


Figure 14 Normalized Maximum Transient Thermal Impedance



PE8208C SOT-23-3L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	1.050	1.100	1.150
A1	0.000	0.050	0.100
L1	0.300	0.400	0.500
C	0.100	0.150	0.200
D	2.820	2.920	3.020
E	1.500	1.600	1.700
E1	2.650	2.800	2.950
B	1.800	1.900	2.000
B1	0.950 TYP.		
L2	0.300	0.450	0.600
O	0°	4°	8°